

DS91D180/DS91C180 100 MHz M-LVDS Line Driver/Receiver Pair

Check for Samples: DS91C180, DS91D180

FEATURES

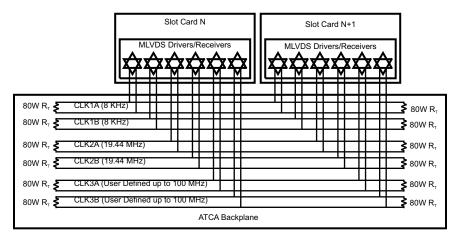
- DC to 100+ MHz / 200+ Mbps Low Power, Low EMI Operation
- Optimal for ATCA, uTCA Clock Distribution Networks
- Meets or Exceeds TIA/EIA-899 M-LVDS Standard
- Wide Input Common Mode Voltage for Increased Noise Immunity
- DS91D180 has Type 1 Receiver Input
- DS91C180 has Type 2 Receiver Input for Fail-Safe Functionality
- Industrial Temperature Range
- Space Saving SOIC-14 Package (JEDEC MS-012)

DESCRIPTION

The DS91D180 and DS91C180 are 100 MHz M-LVDS (Multipoint Low Voltage Differential Signaling) line driver/receiver pairs designed for applications that utilize multipoint networks (e.g. clock distribution in ATCA and uTCA based systems). M-LVDS is a bus interface standard (TIA/EIA-899) optimized for multidrop networks. Controlled edge rates, tight input receiver thresholds and increased drive strength are sone of the key enhancments that make M-LVDS devices an ideal choice for distributing signals via multipoint networks.

The DS91D180/DS91C180 driver input accepts LVTTL/LVCMOS signals and converts them to differential M-LVDS signal levels. The DS91D180/DS91C180 receiver accepts low voltage differential signals (LVDS, B-LVDS, M-LVDS, LV-PECL and CML) and converts them to 3V LVCMOS signals. The DS91D180 device has a M-LVDS type 1 receiver input with no offset. The DS91C180 device has a type 2 receiver input which enable failsafe functionality.

Typical Application in an ATCA Clock Distribution Network



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Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



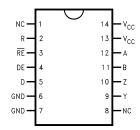


Figure 1. Connection Diagram
Top View
See Package Number D0014A

R A B DE Y

M-LVDS Receiver Types

The EIA/TIA-899 M-LVDS standard specifies two different types of receiver input stages. A type 1 receiver has a conventional threshold that is centered at the midpoint of the input amplitude, $V_{ID}/2$. A type 2 receiver has a built in offset that is 100mV greater than $V_{ID}/2$. The type 2 receiver offset acts as a failsafe circuit where open or short circuits at the input will always result in the output stage being driven to a low logic state.

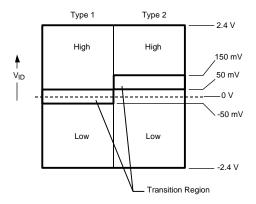


Figure 2. M-LVDS Receiver Input Thresholds



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

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Absolute Maximum Ratings (1)(2)

Supply Voltage, V _{CC}		-0.3V to +4V
Control Input Voltages	-0.3V to (V _{CC} + 0.3V)	
Driver Input Voltage		-0.3V to (V _{CC} + 0.3V)
Driver Output Voltages		-1.8V to +4.1V
Receiver Input Voltages		-1.8V to +4.1V
Receiver Output Voltage		-0.3V to (V _{CC} + 0.3V)
Maximum Package Power Dissipation at +25°C	SOIC Package	1.1 W
	Derate SOIC Package	8.8 mW/°C above +25°C
Thermal Resistance (4-Layer, 2 oz. Cu, JEDEC)	θ_{JA}	113.7 °C/W
	θ_{JC}	36.9 °C/W
Maximum Junction Temperature		150°C
Storage Temperature Range		−65°C to +150°C
Lead Temperature (Soldering, 4 seconds)		260°C
ESD Ratings:	(HBM 1.5kΩ, 100pF)	≥ 5 kV
	(EIAJ 0Ω, 200pF)	≥ 250 V
	(CDM 0Ω, 0pF)	≥ 1000 V

[&]quot;Absolute Maximum Ratings" are those beyond which the safety of the device cannot be ensured. They are not meant to imply that the device should be operated at these limits. The tables of "Electrical Characteristics" provide conditions for actual device operation.

Recommended Operating Conditions

	Min	Тур	Max	Units
Supply Voltage, V _{CC}	3.0	3.3	3.6	V
Voltage at Any Bus Terminal (Separate or Common-Mode)	-1.4		+3.8	V
Differential Input Voltage V _{ID}			2.4	V
High Level Input Voltage V _{IH}	2.0		V _{CC}	V
Low Level Input Voltage V _{IL}	0		0.8	V
Operating Free Air Temperature T _A	-40	+25	+85	°C

Electrical Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified. (1)(2)(3)(4)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
M-LVDS D	river					•
V _{YZ}	Differential output voltage magnitude $R_L = 50\Omega$, $C_L = 5pF$		480		650	mV
ΔV_{YZ}	Change in differential output voltage magnitude between logic states	Figure 3 and Figure 5	-50	0	+50	mV
V _{OS(SS)}	Steady-state common-mode output voltage	$R_L = 50\Omega$, $C_L = 5pF$	0.3	1.8	2.1	V
$ \Delta V_{OS(SS)} $	Change in steady-state common-mode output voltage between logic states Change in steady-state common-mode output voltage between logic states		0		+50	mV
V _{OS(PP)}	Peak-to-peak common-mode output voltage	(V _{OS(pp)} @ 500KHz clock)		143		mV
V _{Y(OC)}	Maximum steady-state open-circuit output voltage	Figure 6	0		2.4	V
V _{Z(OC)}	Maximum steady-state open-circuit output voltage		0		2.4	V
V _{P(H)}	Voltage overshoot, low-to-high level output	$R_L = 50\Omega$, $C_L = 5pF$,			1.2V _{SS}	V
V _{P(L)}	Voltage overshoot, high-to-low level output	C _D = 0.5pF Figure 8 and Figure 9 ⁽⁵⁾	-0.2V _{SS}			V
I _{IH}	High-level input current (LVTTL inputs)	V _{IH} = 2.0V	-15		15	μΑ

⁽¹⁾ All currents into device pins are positive; all currents out of device pins are negative. All voltages are referenced to device ground unless otherwise specified.

Product Folder Links: DS91C180 DS91D180

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If Military/Aerospace specified devices are required, please contact the TI Sales Office/Distributors for availability and specifications.

All typicals are given for $V_{CC} = 3.3V$ and $T_A = 25^{\circ}C$. The algebraic convention, in which the least positive (most negative) limit is designated as minimum, is used in this datasheet.

C_L includes fixture capacitance and C_D includes probe capacitance.

Not production tested. Ensured by a statistical analysis on a sample basis at the time of characterization.



Electrical Characteristics (continued)

Over recommended operating supply and temperature ranges unless otherwise specified. (1)(2)(3)(4)

Symbol	Parameter	Conditions	ì	Min	Тур	Max	Units
I _{IL}	Low-level input current (LVTTL inputs)	V _{IL} = 0.8V		-15		15	μΑ
V _{IKL}	Input Clamp Voltage (LVTTL inputs)	I _{IN} = -18 mA		-1.5			V
los	Differential short-circuit output current	Figure 7		-43		43	mA
M-LVDS R	eceiver	1					.1
V _{IT+}	Positive-going differential input voltage threshold	See Function Tables	Type 1		20	50	mV
			Type 2		94	150	mV
V _{IT} -	Negative-going differential input voltage threshold	See Function Tables	Type 1	-50	20		mV
			Type 2	50	94		mV
V _{OH}	High-level output voltage	I _{OH} = −8mA		2.4	2.7		V
V _{OL}	Low-level output voltage	I _{OL} = 8mA			0.28	0.4	V
l _{OZ}	TRI-STATE output current	V _O = 0V or 3.6V		-10		10	μA
I _{OSR}	Short circuit Rrceiver output current (LVTTL Output)	V _O = 0V		-90	-48		mA
M-LVDS B	us (Input and Output) Pins	1					
I_A , I_Y	Receiver input or driver high-impedance output current	$V_{A,Y} = 3.8V, V_{B,Z} = 1.2V$ DE = GND	/,			32	μΑ
		$V_{A,Y} = 0V \text{ or } 2.4V, V_{B,Z}$ = GND	= 1.2V, DE	-20		+20	μA
		$V_{A,Y} = -1.4V, V_{B,Z} = 1.2V,$ DE = GND		-32			μA
I_B , I_Z	Receiver input or driver high-impedance output current	$V_{B,Z} = 3.8V, V_{A,Y} = 1.2V,$ DE = GND				32	μA
		$V_{B,Z} = 0V$ or 2.4V, $V_{A,Y} = 1.2V$, DE = GND		-20		+20	μA
		$V_{B,Z} = -1.4V, V_{A,Y} = 1.2$ DE = GND	2V,	-32			μA
I _{AB} , I _{YZ}	Receiver input or driver high-impedance output differential current ($I_A - I_B$ or $I_Y - I_Z$)	$V_{A,Y} = V_{B,Z}, -1.4V \le V \le 3.8V, DE = GND$		-4		+4	μΑ
I _{A(OFF)} , I _{Y(OFF)}	Receiver input or driver high-impedance output power-off current	$V_{A,Y} = 3.8V, V_{B,Z} = 1.2V$ DE = 0V 0V \leq V _{CC} \leq 1.5V	/,			32	μΑ
		$V_{A,Y} = 0V \text{ or } 2.4V, V_{B,Z}$ DE = 0V $0V \le V_{CC} \le 1.5V$	= 1.2V,	-20		+20	μА
		$V_{A,Y} = -1.4V, V_{B,Z} = 1.20$ DE = 0V 0V \le V_{CC} \le 1.5V	2V,	-32			μА
$I_{B(OFF)},\\I_{Z(OFF)}$	Receiver input or driver high-impedance output power-off current	$V_{B,Z} = 3.8V, V_{A,Y} = 1.2V$ DE = 0V $0V \le V_{CC} \le 1.5V$	/,			32	μА
		$V_{B,Z} = 0V \text{ or } 2.4V, V_{A,Y}$ DE = 0V $0V \le V_{CC} \le 1.5V$	= 1.2V,	-20		+20	μА
		$V_{B,Z} = -1.4V, V_{A,Y} = 1.2$ DE = 0V 0V \le V_{CC} \le 1.5V	2V,	-32			μА
I _{AB(OFF)} , I _{YZ(OFF)}	Receiver input or driver high-impedance output power-off differential current (I _{A(OFF)} - I _{B(OFF)} or I _{Y(OFF)} - I _{Z(OFF)})	$V_{A,Y} = V_{B,Z}$, $-1.4V \le V \le 3.8V$, DE = 0V $0V \le V_{CC} \le 1.5V$		-4		+4	μΑ
C _A , C _B	Receiver input capacitance	V _{CC} = OPEN			5.1		pF
C _Y , C _Z	Driver output capacitance				8.5		pF
C _{AB}	Receiver input differential capacitance				2.5		pF
C _{YZ}	Driver output differential capacitance				5.5		pF



Electrical Characteristics (continued)

Over recommended operating supply and temperature ranges unless otherwise specified. (1)(2)(3)(4)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
C _{A/B} , C _{Y/Z}	Receiver input or driver output capacitance balance $(C_A/C_B \text{ or } C_Y/C_Z)$			1.0		
SUPPLY C	URRENT (V _{CC})		*			
I _{CCD}	Driver Supply Current	$R_L = 50\Omega$, $DE = V_{CC}$, $\overline{RE} = V_{CC}$		17	29.5	mA
I _{CCZ}	TRI-STATE Supply Current	DE = GND, RE = V _{CC}		7	9.0	mA
I _{CCR}	Receiver Supply Current	DE = GND, RE = GND		14	18.5	mA
I _{CCB}	Supply Current, Driver and Receiver Enabled	$DE = V_{CC}, \overline{RE} = GND$		20	29.5	mA

Switching Characteristics

Over recommended operating supply and temperature ranges unless otherwise specified. (1) (2)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
DRIVER AC S	SPECIFICATION		•		•	*
t _{PLH}	Differential Propagation Delay Low to High	$R_L = 50\Omega$, $C_L = 5 pF$,	1.0	3.4	5.5	ns
t _{PHL}	Differential Propagation Delay High to Low	$C_D = 0.5 \text{ pF}$	1.0	3.1	5.5	ns
$t_{SKD1} (t_{sk(p)})$	Pulse Skew t _{PLHD} - t _{PHLD} (3) (4)	Figure 8 and Figure 9		300	420	ps
t _{SKD3}	Part-to-Part Skew (5) (4)				1.9	ns
t_{TLH} (t_r)	Rise Time (4)		1.0	1.8	3.0	ns
t _{THL} (t _f)	Fall Time (4)		1.0	1.8	3.0	ns
t _{PZH}	Enable Time (Z to Active High) $R_L = 50\Omega$, $C_L = 5$ pF,				8	ns
t _{PZL}	Enable Time (Z to Active Low)	$C_D = 0.5 \text{ pF}$			8	ns
t _{PLZ} Disable Time (Active Low to Z)		Figure 10 and Figure 11			8	ns
t _{PHZ}	Disable Time (Active High to Z)				8	ns
t _{JIT}	Random Jitter, RJ (4)	100MHz clock pattern ⁽⁶⁾		2.5	5.5	psrms
f _{MAX}	Maximum Data Rate		200			Mbps
RECEIVER A	C SPECIFICATION					
t _{PLH}	Propagation Delay Low to High	C _L = 15 pF	2.0	4.7	7.5	ns
t _{PHL}	Propagation Delay High to Low	Figure 12 Figure 13 and Figure 14	2.0	5.3	7.5	ns
t _{SKD1} (t _{sk(p)})	Pulse Skew t _{PLHD} - t _{PHLD} (3)(4)			0.6	1.9	ns
t _{SKD3}	Part-to-Part Skew (5)(4)				1.5	ns
t _{TLH} (t _r)	Rise Time ⁽⁴⁾		0.5	1.2	3.0	ns
t _{THL} (t _f)	Fall Time ⁽⁴⁾		0.5	1.2	3.0	ns
t _{PZH}	Enable Time (Z to Active High)	$R_L = 500\Omega$, $C_L = 15 pF$			10	ns
t _{PZL}	Enable Time (Z to Active Low)	Figure 15 and Figure 16			10	ns
t _{PLZ}	Disable Time (Active Low to Z)				10	ns
t _{PHZ}	Disable Time (Active High to Z)				10	ns
f _{MAX}	Maximum Data Rate		200			Mbps

⁽¹⁾ All typicals are given for V = 3.3V and $T_A = 25$ °C.

⁽²⁾ C_L includes fixture capacitance and C_D includes probe capacitance.

⁽³⁾ t_{SKD1}, |t_{PLHD} - t_{PHLD}|, is the magnitude difference in differential propagation delay time between the positive going edge and the negative going edge of the same channel.

⁽⁴⁾ Not production tested. Ensured by a statistical analysis on a sample basis at the time of characterization.

⁽⁵⁾ t_{SKD3}, Part-to-Part Skew, is defined as the difference between the minimum and maximum specified differential propagation delays. This specification applies to devices at the same V_{CC} and within 5°C of each other within the operating temperature range.

⁽⁶⁾ Stimulus and fixture jitter has been subtracted.



Test Circuits and Waveforms

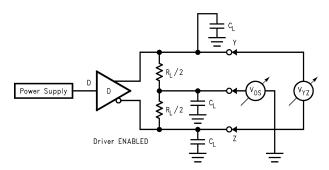


Figure 3. Differential Driver Test Circuit

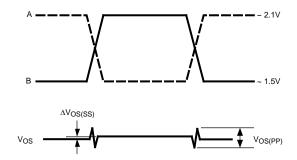


Figure 4. Differential Driver Waveforms

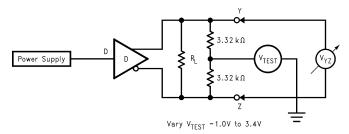


Figure 5. Differential Driver Full Load Test Circuit

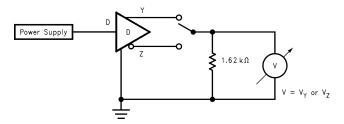


Figure 6. Differential Driver DC Open Test Circuit



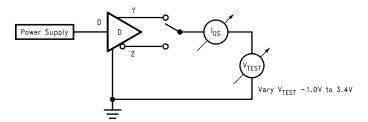


Figure 7. Differential Driver Short-Circuit Test Circuit

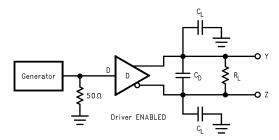


Figure 8. Driver Propagation Delay and Transition Time Test Circuit

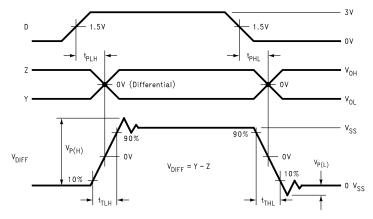


Figure 9. Driver Propagation Delays and Transition Time Waveforms

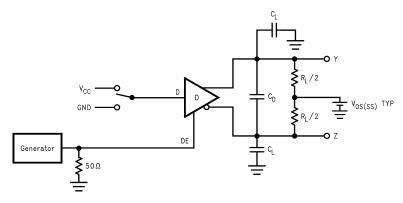


Figure 10. Driver TRI-STATE Delay Test Circuit



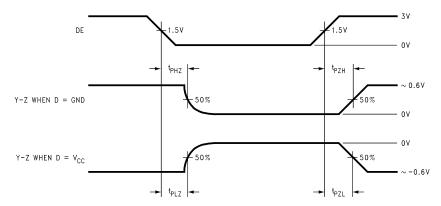


Figure 11. Driver TRI-STATE Delay Waveforms

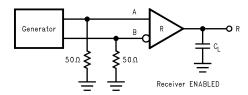


Figure 12. Receiver Propagation Delay and Transition Time Test Circuit

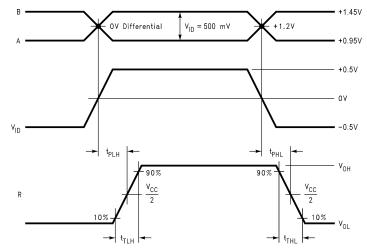


Figure 13. Type 1 Receiver Propagation Delay and Transition Time Waveforms



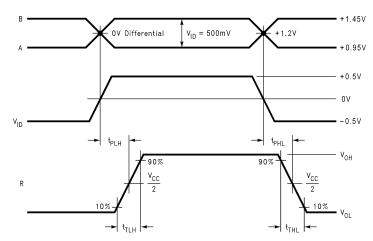


Figure 14. Type 2 Receiver Propagation Delay and Transition Time Waveforms

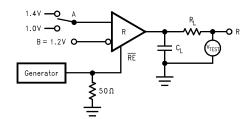


Figure 15. Receiver TRI-STATE Delay Test Circuit

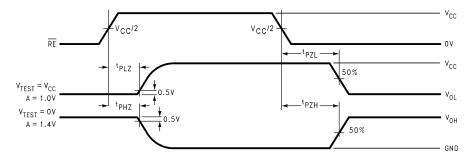


Figure 16. Receiver TRI-STATE Delay Waveforms



FUNCTION TABLES

Table 1. DS91D180/DS91C180 Transmitting(1)

Inp	outs	Out	puts
DE	D	Z	Υ
2.0V	2.0V	L	Н
2.0V	0.8V	Н	L
0.8V	Х	Z	Z

(1) X — Don't care condition

Z — High impedance state

Table 2. DS91D180 Receiving⁽¹⁾

Inputs		Output
RE	A - B	R
0.8V	≥ +0.05V	Н
0.8V	≤ - 0.05V	L
0.8V	0V	X
2.0V	X	Z

(1) X — Don't care condition

Z — High impedance state

Table 3. DS91C180 Receiving⁽¹⁾

Inputs		Output
RE	A - B	R
0.8V	≥ +0.15V	Н
0.8V	≤ +0.05V	L
0.8V	0V	L
2.0V	X	Z

(1) X — Don't care condition Z — High impedance state

Table 4. DS91D180 Receiver Input Threshold Test Voltages⁽¹⁾

Applied	Voltages	Resulting Differential Input Voltage	Resulting Common-Mode Input Voltage	Receiver Output
V _{IA}	V _{IB}	V _{ID}	V _{IC}	R
2.400V	0.000V	2.400V	1.200V	Н
0.000V	2.400V	-2.400V	1.200V	L
3.800V	3.750V	0.050V	3.775V	Н
3.750V	3.800V	-0.050V	3.775V	L
-1.400V	-1.350V	-0.050V	−1.375V	Н
-1.350V	-1.400V	0.050V	-1.375V	L

(1) H — High Level L — Low Level

Output state assumes that the receiver is enabled ($\overline{RE} = L$)

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Table 5. DS91C180 Receiver Input Threshold Test Voltages (1)

Applied	Voltages	Resulting Differential Input Voltage	Resulting Common-Mode Input Voltage	Receiver Output
V _{IA}	V_{IB}	V _{ID}	V _{IC}	R
2.400V	0.000V	2.400V	1.200V	Н
0.000V	2.400V	-2.400V	1.200V	L
3.800V	3.650V	0.150V	3.725V	Н
3.800V	3.750V	0.050V	3.775V	L
-1.250V	-1.400V	0.150V	-1.325V	Н
-1.350V	-1.400V	0.050V	-1.375V	L

⁽¹⁾ H — High Level L — Low Level

Output state assumes that the receiver is enabled ($\overline{RE} = L$)

PIN DESCRIPTIONS

Pin No.	Name	Description
1, 8	NC	No connect.
2	R	Receiver output pin
3	RE	Receiver enable pin: When \overline{RE} is high, the receiver is disabled. When \overline{RE} is low or open, the receiver is enabled.
4	DE	Driver enable pin: When DE is low, the driver is disabled. When DE is high, the driver is enabled.
5	D	Driver input pin
6, 7	GND	Ground pin
9	Y	Non-inverting driver output pin
10	Z	Inverting driver output pin
11	В	Inverting receiver input pin
12	А	Non-inverting receiver input pin
13, 14	V _{CC}	Power supply pin, +3.3V ± 0.3V

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SNLS158M - MARCH 2006-REVISED APRIL 2013



REVISION HISTORY

Cr	nanges from Revision L (April 2013) to Revision M	Pa	ıge
•	Changed layout of National Data Sheet to TI format		11





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
DS91C180TMA/NOPB	ACTIVE	SOIC	D	14	55	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91C180 TMA	Samples
DS91C180TMAX/NOPB	ACTIVE	SOIC	D	14	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91C180 TMA	Samples
DS91D180TMA/NOPB	ACTIVE	SOIC	D	14	55	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91D180 TMA	Samples
DS91D180TMAX/NOPB	ACTIVE	SOIC	D	14	2500	RoHS & Green	SN	Level-1-260C-UNLIM	-40 to 85	DS91D180 TMA	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

10-Dec-2020

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TAPE AND REEL INFORMATION





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		Dimension designed to accommodate the component width
	B0	Dimension designed to accommodate the component length
	K0	Dimension designed to accommodate the component thickness
	W	Overall width of the carrier tape
ı	P1	Pitch between successive cavity centers

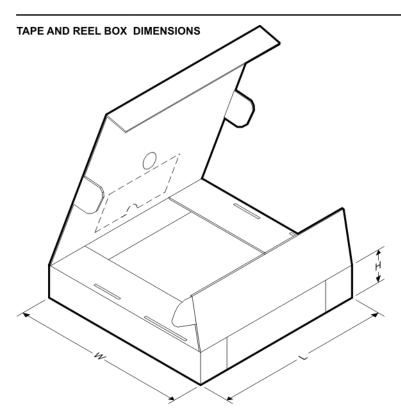
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DS91C180TMAX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1
DS91D180TMAX/NOPB	SOIC	D	14	2500	330.0	16.4	6.5	9.35	2.3	8.0	16.0	Q1

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DS91C180TMAX/NOPB	SOIC	D	14	2500	367.0	367.0	35.0
DS91D180TMAX/NOPB	SOIC	D	14	2500	356.0	356.0	35.0

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
DS91C180TMA/NOPB	D	SOIC	14	55	495	8	4064	3.05
DS91D180TMA/NOPB	D	SOIC	14	55	495	8	4064	3.05

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



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